-	21	(semiconductor near laser) and (active near (layer or region	USPAT;	2003/04/04 10:46
		or medium or film)) and (protection near (film or layer or	US-PGPUB;	
		region or medium)) and ridge and (refractive near (index or	EPO; JPO;	
		indice)) and (open\$5) and (shap\$4)	DERWENT;	
			IBM_TDB	
-	3	("5029175" "5474954" "5805627").PN.	USPAT	2003/04/04 10:40
-	23	(semiconductor near laser) and (active near (layer or region	USPAT;	2003/04/04 10:49
		or medium or film)) and (protection near (film or layer or	US-PGPUB;	
l		region or medium)) and ridge and (refractive near (index or	EPO; JPO;	
		indice)) and (open\$5) and (shap\$4) and width	DERWENT;	
· .			IBM_TDB	
-	57	(semiconductor near laser) and substrate and (active near	USPAT;	2003/04/04 11:06
		(layer or region or film or medium)) and (protection near	US-PGPUB;	
		(layer or region or film or medium)) and (ridge or stripe)	EPO; JPO;	
		and (refractive near (index or indice)) and width	DERWENT;	
			IBM_TDB	
-	18	(semiconductor near laser) and substrate and (active near	USPAT;	2003/04/04 12:09
		(layer or region or film or medium)) and (protection near	US-PGPUB;	
		(layer or region or film or medium)) and ((ridge or stripe)	EPO; JPO;	
		WITH (refractive near (index or indice))) and width	DERWENT;	
			IBM_TDB	0000104104040
-	14	(semiconductor near laser) and substrate and (protection	USPAT;	2003/04/04 12:40
		near (layer or region or film or medium)) and ((ridge or	US-PGPUB;	
		stripe) WITH (refractive near (index or indice)) WITH	EPO; JPO;	
		(active near (layer or region or film or medium))) and width	DERWENT;	
			IBM_TDB	2002/11/12 00:21
-	405	(semiconductor near laser) and (active near (layer or region	USPAT;	2003/11/13 09:31
		or medium or film)) and ((protect\$4 or dielectric) near	US-PGPUB;	
		(film or layer or region or medium)) and ridge and	EPO; JPO;	
		(refractive near (index or indice))	DERWENT;	
		(comband star par lacer) and (active par (laver or region	IBM_TDB USPAT;	2003/11/13 10:34
-	61	(semiconductor near laser) and (active near (layer or region	US-PGPUB;	2003/11/13 10:34
		or medium or film)) and (protection near2 (film or layer or	EPO; JPO;	
		region or medium)) and ridge and (refractive near (index or	DERWENT;	
		indice))	IBM_TDB	
	5	(comissanductor poor lacer) and (active poor (laver or region	USPAT;	2003/11/14 06:09
-	5	(semiconductor near laser) and (active near (layer or region or medium or film)) and (protection near2 dielectric near2	US-PGPUB;	2003/11/17 00:03
		(film or layer or region or medium)) and ridge and	EPO; JPO;	
		(nim or layer or region or median)) and hage and (refractive near (index or indice))	DERWENT;	
		(Terractive fied)	IBM_TDB	
L	L		עטו_ויוטנ	<u> </u>

L Number	Hits	Search Text	DB	Time stamp
-	34	(semiconductor near laser) and (active near (layer or region	USPAT;	2003/11/13 09:51
		or medium or film)) and (protection near (film or layer or	US-PGPUB;	
		region or medium)) and ridge and (refractive near (index or	EPO; JPO;	
		indice))	DERWENT;	
		"	IBM_TDB	
_	28	((semiconductor near laser) and (active near (layer or region	USPAT;	2002/05/20 13:54
		or medium or film)) and (protection near (film or layer or	US-PGPUB;	
		region or medium)) and ridge and (refractive near (index or	EPO; JPO;	
		indice))) and width	DERWENT;	
		indice))) and width		
-	40	(IBM_TDB	2002/05/20 10:27
	12	(semiconductor near laser) and ((active near (layer or region	USPAT;	2002/05/20 10:37
		or medium or film)) SAME (protection near (film or layer	US-PGPUB;	
		or region or medium)) SAME (SUBSTRATE)) and ridge and	EPO; JPO;	
		(refractive near (index or indice))	DERWENT;	
			IBM_TDB	
-	21	(semiconductor near laser) and ((active near (layer or region	USPAT;	2002/05/20 15:02
		or medium or film)) AND (protection near (film or layer or	US-PGPUB;	, ,
		region or medium)) SAME (SUBSTRATE)) and ridge and	EPO; JPO;	
		(refractive near (index or indice))	DERWENT;	
İ		(rendetive near (index or indice))	IBM_TDB	
	17	(/cominanductor poor locar) and (/active poor (laver or		2002/05/20 14/24
-	17	((semiconductor near laser) and ((active near (layer or	USPAT;	2002/05/20 14:24
		region or medium or film)) AND (protection near (film or	US-PGPUB;	
		layer or region or medium)) SAME (SUBSTRATE)) and ridge	EPO; JPO;	
		and (refractive near (index or indice))) and width	DERWENT;	
			IBM_TDB	
-	10	((semiconductor near laser) and ((active near (layer or	USPAT;	2002/05/20 14:24
İ		region or medium or film)) SAME (protection near (film or	US-PGPUB;	
		layer or region or medium)) SAME (SUBSTRATE)) and ridge	EPO; JPO;	
i		and (refractive near (index or indice))) and width	DERWENT;	
		and (remains near (mass or maiss)) / and mass	IBM_TDB	
	12	(semiconductor near laser) and ((active near (layer or region	USPAT;	2002/05/20 16:36
	12	or medium or film)) AND (protection near (film or layer or	US-PGPUB;	2002/03/20 10.30
1				
		region or medium)) SAME (SUBSTRATE)) and (width same	EPO; JPO;	
		ridge) and (refractive near (index or indice))	DERWENT;	
			IBM_TDB	
-	11	((semiconductor near laser) and ((active near (layer or	USPAT;	2002/05/21 08:26
		region or medium or film)) AND (protection near (film or	US-PGPUB;	
		layer or region or medium)) SAME (SUBSTRATE)) and (EPO; JPO;	
		width same ridge) and (refractive near (index or indice)))	DERWENT;	
		and 372/\$	IBM_TDB	
_	456	(semiconductor near laser) and (active near (layer or region	USPAT;	2002/05/21 10:56
	.55	or medium or film)) and ((dielectric or insulat\$5 or	US-PGPUB;	,,,
Ī		protect\$5) near (film or layer or region or medium)) and	EPO; JPO;	
		ridge and (refractive near (index or indice))	DERWENT;	
1		riuge and (retractive fiear (index or indice))		
•	202		IBM_TDB	2002/05/24 40 50
-	382	(semiconductor near laser) and (active near (layer or region	USPAT;	2002/05/21 10:59
		or medium or film)) and ((dielectric or insulat\$5 or	US-PGPUB;	
		protect\$5) near (film or layer or region or medium)) and	EPO; JPO;	
		ridge and (refractive near (index or indice)) AND substrate	DERWENT;	
		and width	IBM_TDB	
-	0	(semiconductor near laser) and (active near (layer or region	USPAT;	2002/05/22 13:14
	-	or medium or film)) and (((dielectric or insulat\$5 or	US-PGPUB;	
	l	protect\$5) near (film or layer or region or medium)) same	EPO; JPO;	
	l			
	l	substrat) and ridge and (refractive near (index or indice))	DERWENT;	
ļ	20.4	and width	IBM_TDB	2002/05/22 42 42
-	284	(semiconductor near laser) and (active near (layer or region	USPAT;	2002/05/22 13:18
	l	or medium or film)) and (((dielectric or insulat\$5 or	US-PGPUB;	
	l	protect\$5) near (film or layer or region or medium)) same	EPO; JPO;	
	i	substrate) and ridge and (refractive near (index or indice))	DERWENT;	
:		and width	IBM_TDB	

			1	200010710010
-	131	(semiconductor near laser) and (active near (layer or region	USPAT;	2002/05/22 13:21
		or medium or film)) and (((dielectric or insulat\$5 or	US-PGPUB;	
		protect\$5) near (film or layer or region or medium)) same	EPO; JPO;	
		substrate same ridge) and (refractive near (index or indice))	DERWENT;	
		and width	IBM_TDB	
-	29	(semiconductor near laser) and (active near (layer or region	USPAT;	2002/05/22 14:31
		or medium or film)) and (((dielectric or insulat\$5 or	US-PGPUB;	
		protect\$5) near (film or layer or region or medium)) same	EPO; JPO;	
		substrate same ridge same (refractive near (index or	DERWENT;	
		indice))) and width	IBM_TDB	
_	23	((semiconductor near laser) and (active near (layer or region	USPAT;	2002/05/22 14:31
		or medium or film)) and (((dielectric or insulat\$5 or	US-PGPUB;	, ,
		protect\$5) near (film or layer or region or medium)) same	EPO; JPO;	
		substrate same ridge same (refractive near (index or	DERWENT;	
		indice))) and width) and 372/\$	IBM_TDB	
1_	6	((semiconductor near laser) and (active near (layer or region	USPAT;	2002/05/22 14:32
		or medium or film)) and (((dielectric or insulat\$5 or	US-PGPUB;	2002/05/22 11:52
		protect\$5) near (film or layer or region or medium)) same	EPO; JPO;	
		1, , , , , , , , , , , , , , , , , , ,	DERWENT;	
		substrate same ridge same (refractive near (index or	IBM_TDB	
	13	indice))) and width) and 257/\$	USPAT;	2002/05/22 14:36
1-	12	(semiconductor near device) and (active near (layer or	US-PGPUB;	2002/03/22 17.30
		region or medium or film)) and (((dielectric or insulat\$5 or		
	and the second	protect\$5) near (film or layer or region or medium)) same	EPO; JPO;	
		substrate same ridge same (refractive near (index or	DERWENT;	
	20	indice))) and width	IBM_TDB	2002/05/22 44.44
-	30	(semiconductor near (device or laser)) and (active near	USPAT;	2002/05/22 14:41
		(layer or region or medium or film)) and (((dielectric or	US-PGPUB;	
		insulat\$5 or protect\$5) near (film or layer or region or	EPO; JPO;	
		medium)) same substrate same ridge same (refractive near	DERWENT;	
	_	(index or indice))) and width	IBM_TDB	
-	344	(semiconductor with optical) and substrate and (active near	USPAT;	2002/05/31 10:54
·		(layer or film or region or medium)) and ((protect\$5 or	US-PGPUB;	
ļ		insulat\$5) near (film or layer or region or medium)) and	EPO; JPO;	
		ridge and refractive	DERWENT;	
			IBM_TDB	
-	114	(semiconductor with optical) and substrate and (active near	USPAT;	2002/05/31 13:23
		(layer or film or region or medium)) and ((protect\$5 or	US-PGPUB;	
		insulat\$5) near (film or layer or region or medium)) and	EPO; JPO;	
		(ridge or groove) and refractive and (stripe near shaped)	DERWENT;	
			IBM_TDB	
-	0	((semiconductor with optical) and substrate and (active near	USPAT;	2002/05/31 13:33
		(layer or film or region or medium)) and ((protect\$5 or	US-PGPUB;	
		insulat\$5) near (film or layer or region or medium)) and	EPO; JPO;	
		(ridge or groove) and refractive and (stripe near shaped))	DERWENT;	
		and (open\$5 near center) and (open\$5 near rear)	IBM_TDB	
-	108	((semiconductor with optical) and substrate and (active near	USPAT;	2002/05/31 13:38
		(layer or film or region or medium)) and ((protect\$5 or	US-PGPUB;	
		insulat\$5) near (film or layer or region or medium)) and	EPO; JPO;	
		(ridge or groove) and refractive and (stripe near shaped))	DERWENT;	
		and width	IBM_TDB	
-	90	(((semiconductor with optical) and substrate and (active	USPAT;	2002/05/31 13:38
		near (layer or film or region or medium)) and ((protect\$5 or	US-PGPUB;	, ,
		insulat\$5) near (film or layer or region or medium)) and	EPO; JPO;	
		(ridge or groove) and refractive and (stripe near shaped))	DERWENT;	
		and width) and 372/\$	IBM_TDB	
_	27	(semiconductor near laser) and (active near (layer or region	USPAT;	2002/06/18 11:28
	-/	or medium or film)) and (protection near (film or layer or	US-PGPUB;	
		region or medium)) and ridge and (refractive near (index or	EPO; JPO;	
		indice)) and (open\$5)	DERWENT;	
		Indias) did (opensy)	IBM_TDB	
	I		100	<u> </u>